MOS FET

FJ6K01010L

Panasonic

FJ6K01010L

Silicon P-channel MOS FET

For switching

■ Features

- Low drain-source On-state resistance : RDS (on) typ. = 26 m Ω (VGS = -4.5 V)
- Low drive voltage: 1.8 V drive
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol : T4

Established: 2010-04-05

: 2013-07-01

Revised

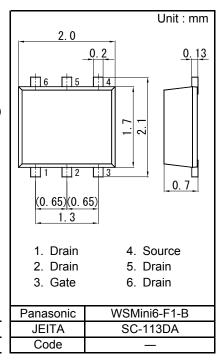
■ Packaging

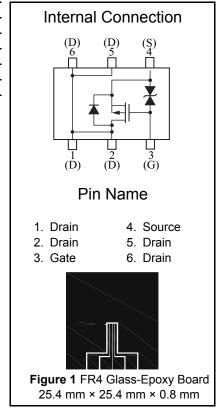
Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Drain-source voltage	VDS	-12	V
Gate-source voltage	VGS	±8	V
Drain current	ID	-4.0	Α
Pulse drain current	IDp	-20	Α
Total power dissipation *1	PD	700	mW
Channel temperature	Tch	150	°C
Operating ambient temperature	Topr	-40 to + 85	°C
Storage temperature	Tstg	-55 to +150	°C

Note) *1 Measuring on Glass epoxy board (25.4 x 25.4 x 0.8 mm) (See Figure 1)
Absolute maximum rating without heat sink for PD is 150 mW





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MOS FET FJ6K01010L

Page 2 of 6

■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source breakdown voltage	VDSS	ID = -1 mA, VGS = 0	-12			V
Drain-source cutoff current	IDSS	VDS = -10 V, VGS = 0			-1.0	μΑ
Gate-source cutoff current	IGSS	$VGS = \pm 8 \text{ V, VDS} = 0$			±10	μΑ
Gate threshold voltage	Vth	ID = -1.0 mA, VDS = -6.0 V	-0.3	-0.65	-1.0	V
	RDS(on)1	ID = -1.0 A, VGS = -4.5 V		26	34	
Drain-source ON resistance	RDS(on)2	ID = -0.5 A, VGS = -2.5 V		30	41	mΩ
	RDS(on)3	ID = -0.5 A, VGS = -1.8 V		36	54	
Forward transfer admittance	Yfs	ID = -1.0 A, VDS = -10 V	4.0			S
Input capacitance	Ciss			1 400		pF
Output capacitance	Coss	VDS = -10 V, VGS = 0, f = 1 MHz		190		pF
Reverse transfer capacitance	Crss			210		pF
Turn-on delay time *1	td(on)	VDD = -6 V, VGS = 0 to -4 V		9		ns
Rise time *1	tr	ID = -1.0 A		40		ns
Turn-off delay time *1	td(off)	VDD = -6 V, VGS = -4 to 0 V		250		ns
Fall time *1	tf	ID = -1.0 A		150		ns

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

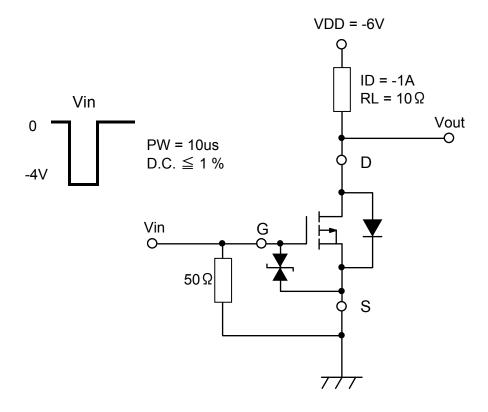
Established: 2010-04-05

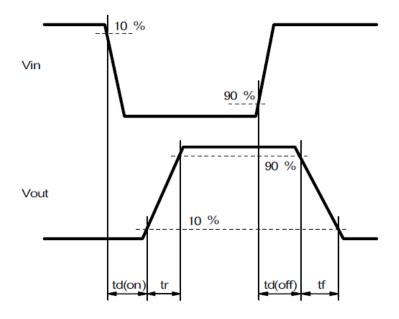
Revised

: 2013-07-01

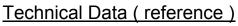
^{2. *1} Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

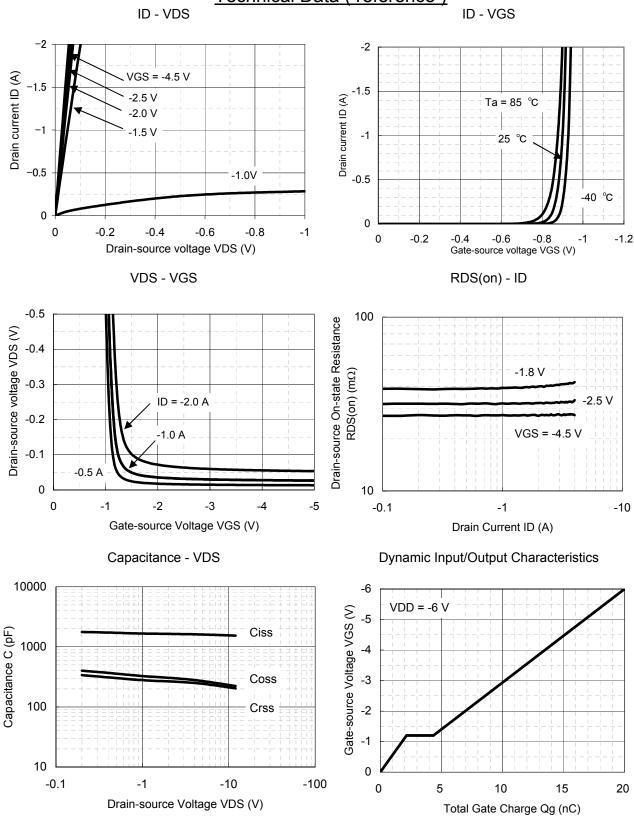
*1 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time





MOS FET FJ6K01010L

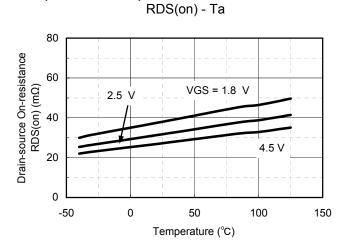




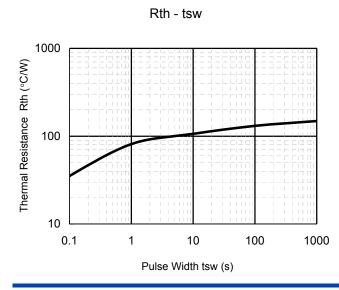
Page 4 of 6

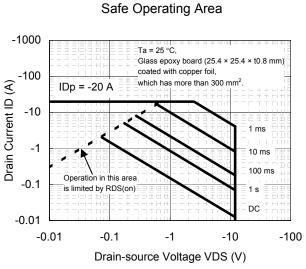
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Technical Data (reference)



Temperature Ta (°C)



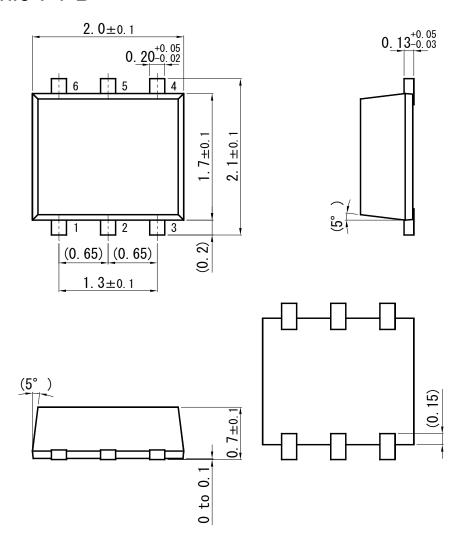


Page 5 of 6

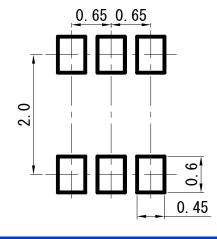
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WSMini6-F1-B

Unit: mm



■Land Pattern (Reference) (Unit : mm)



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